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TOSHIBA Field Effect Transistor Silicon N Channel MOS Type ($L^2-\pi$ -MOSV)

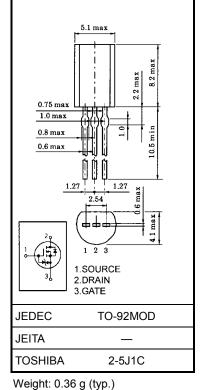
2SK2961

Relay Drive, Motor Drive and DC–DC Converter Application

- Low drain-source ON resistance : RDS (ON) = 0.2 Ω (typ.)
- High forward transfer admittance : $|Y_{fs}| = 2.0 \text{ S (typ.)}$
- Low leakage current $: I_{DSS} = 100 \ \mu A \ (V_{DS} = 60 \ V)$
- Enhancement-mode : $V_{th} = 0.8 \sim 2.0 V (V_{DS} = 10 V, I_D = 1 mA)$

Maximum Ratings (Ta = 25°C)

Characteris	stics	Symbol	Rating	Unit	
Drain-source voltage		V _{DSS}	60	V	
Drain-gate voltage (R	_{GS} = 20 kΩ)	V _{DGR}	60	V	
Gate-source voltage		V _{GSS}	±20	V	
Drain current	DC (Note 1)	۱ _D	2.0	А	
	Pulse (Note 1)	I _{DP}	6.0	A	
Drain power dissipation	ı	PD	0.9	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch−a)}	138	°C/W

Note 1: Please use devices on condition that the channel temperature is below 150°C.

This transistor is an electrostatic sensitive device. Please handle with caution. Unit: mm

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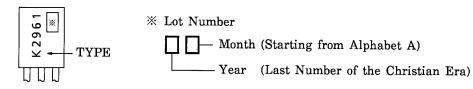
Electrical Characteristics (Ta = 25°C)

Charao	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V		—	±10	μA	
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V	-	_	100	μA	
Drain-source br	eakdown voltage	V (BR) DSS	I _D = 10 mA, V _{GS} = 0 V	60	_		V	
Gate threshold v	voltage	V _{th}	V _{DS} = 10 V, I _D = 1 mA	0.8	_	2.0	V	
Drain-source ON resistance		R _{DS (ON)}	V _{GS} = 4 V, I _D = 1.0 A		0.26	0.38	Ω	
			V _{GS} = 10 V, I _D = 1.0 A	_	0.20	0.27		
Forward transfe	r admittance	Y _{fs}	V _{DS} = 10 V, I _D = 1.0 A	1.0	2.0	—	S	
Input capacitance		Ciss		_	170		pF	
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz	_	25	_		
Output capacitance		C _{oss}			75	_		
Switching time	Rise time	tr	$v_{GS} \xrightarrow{10V}_{0V} \prod_{\substack{I_D = 1A \\ V \cup U \cup V \cup U}} v_{OUT}$	_	10	_		
	Turn-on time	t _{on}		_	15	_	ns	
	Fall time	t _f		_	50	_		
	Turn-off time	t _{off}	Duty $\leq 1\%$, t _w =10µs	_	170	_		
Total gate charge (gate-source plus gate-drain)		Qg		_	5.8	_		
Gate-source charge		Q _{gs}	V _{DD} ≈ 48 V, V _{GS} = 10 V, I _D = 2 A		4.1	_	nC	
Gate-drain ("miller") Charge		Q _{gd}			1.7	_		

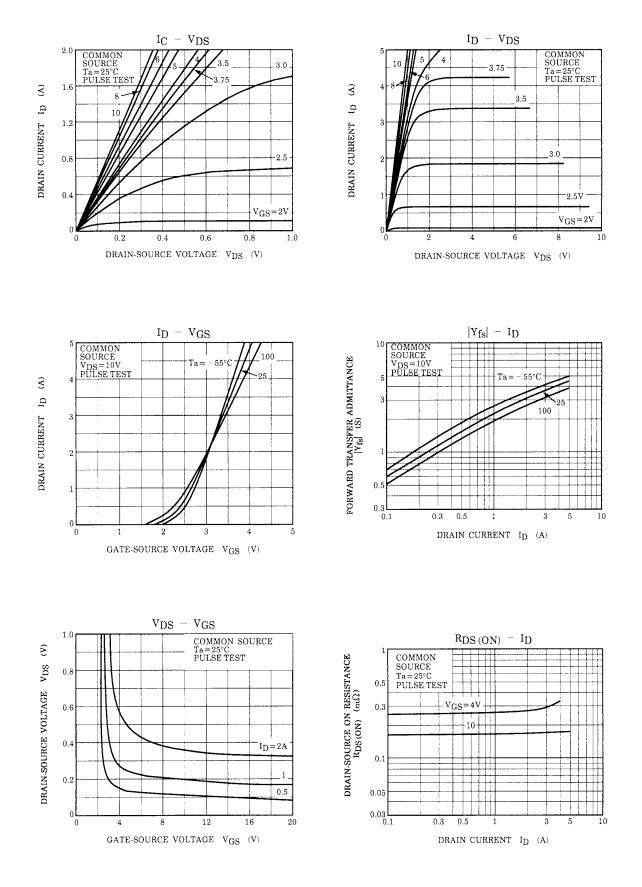
Source–Drain Ratings and Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	—	_	_	2.0	А
Pulse drain reverse current (Note 1)	I _{DRP}	—	_	_	6.0	А
Forward voltage (diode)	V _{DSF}	I _{DR} = 2 A, V _{GS} = 0 V	_	—	-1.5	V
Reverse recovery time	t _{rr}	I _{DR} = 2 A, V _{GS} = 0 V, dI _{DR} / dt = 50 A / µs	_	45	_	ns
Reverse recovery charge	Q _{rr}	$1DR = 2A$, $VGS = 0V$, $0DR / 01 = 50A / \mu s$		40.5		nC

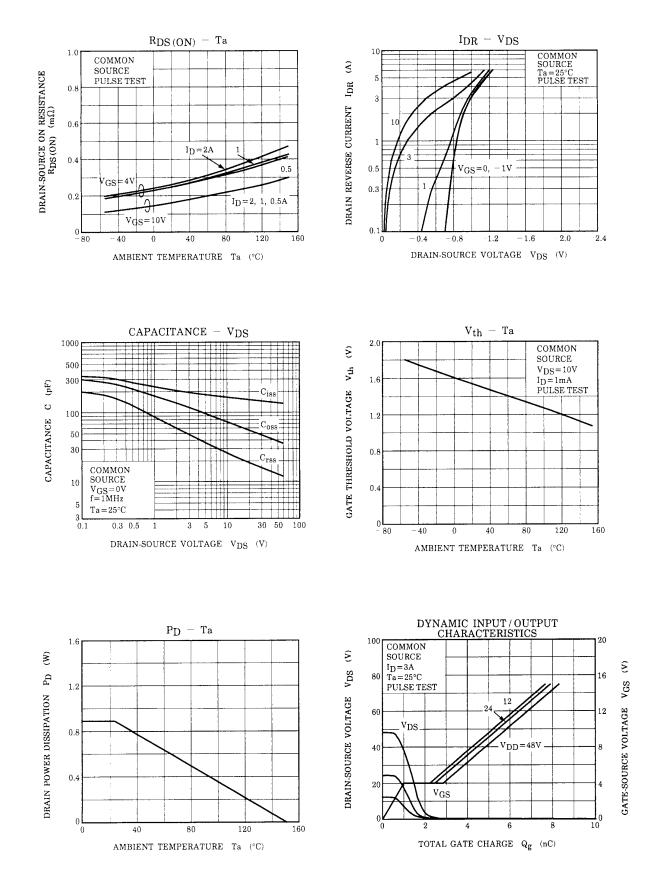
Marking

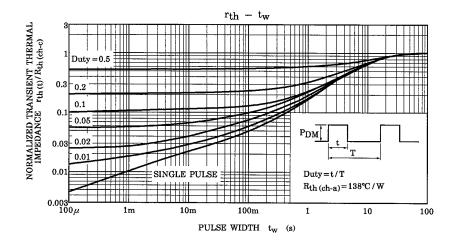


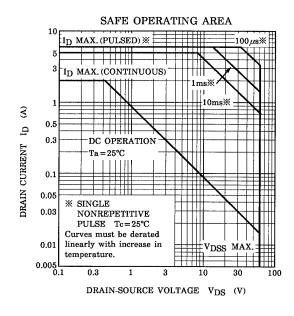
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